

## 9A High-Speed MOSFET Drivers

#### **Features**

- High Peak Output Current: 10A (typ.)
- Low Shoot-Through/Cross-Conduction Current in Output Stage
- Wide Input Supply Voltage Operating Range:
  - 4.5V to 18V
- High Continuous Output Current: 2A (max.)
- · Matched Fast Rise and Fall Times:
  - 15 ns with 4,700 pF Load
  - 135 ns with 47,000 pF Load
- Matched Short Propagation Delays: 42 ns (typ.)
- Low Supply Current:
  - With Logic '1' Input 130 μA (typ.)
  - With Logic '0' Input 33 µA (typ.)
- Low Output Impedance: 1.2Ω (typ.)
- Latch-Up Protected: Will Withstand 1.5A Output Reverse Current
- Input Will Withstand Negative Inputs Up To 5V
- Pin-Compatible with the TC4420/TC4429 and TC4421/TC4422 MOSFET Drivers
- Space-Saving, Thermally-Enhanced, 8-Pin DFN Package

#### **Applications**

- · Line Drivers for Extra Heavily-Loaded Lines
- Pulse Generators
- Driving the Largest MOSFETs and IGBTs
- · Local Power ON/OFF Switch
- · Motor and Solenoid Driver
- LF Initiator

#### **General Description**

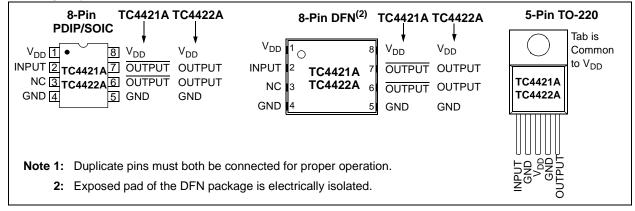
The TC4421A/TC4422A are improved versions of the earlier TC4421/TC4422 family of single-output MOSFET drivers. These devices are high-current buffer/drivers capable of driving large MOSFETs and Insulated Gate Bipolar Transistors (IGBTs). The TC4421A/TC4422A have matched output rise and fall times, as well as matched leading and falling-edge propagation delay times. The TC4421A/TC4422A devices also have very low cross-conduction current, reducing the overall power dissipation of the device.

These devices are essentially immune to any form of upset, except direct overvoltage or over-dissipation. They cannot be latched under any conditions within their power and voltage ratings. These parts are not subject to damage or improper operation when up to 5V of ground bounce is present on their ground terminals. They can accept, without damage or logic upset, more than 1A inductive current of either polarity being forced back into their outputs. In addition, all terminals are fully protected against up to 4 kV of electrostatic discharge.

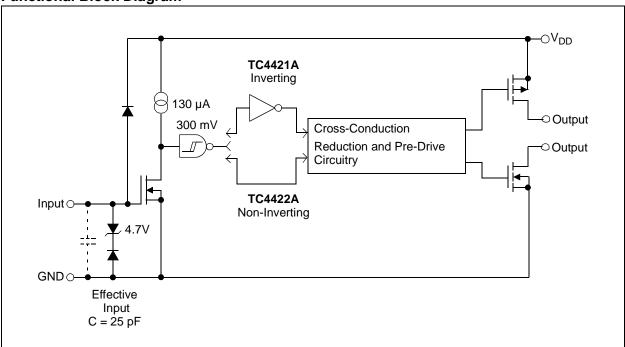
The TC4421A/TC4422A inputs may be driven directly from either TTL or CMOS (3V to 18V). In addition, 300 mV of hysteresis is built into the input, providing noise immunity and allowing the device to be driven from slowly rising or falling waveforms.

With both surface-mount and pin-through-hole packages, in addition to a wide operating temperature range, the TC4421A/TC4422A family of 9A MOSFET drivers fit into most any application where high gate/line capacitance drive is required.

#### Package Types<sup>(1)</sup>



#### **Functional Block Diagram**



## 1.0 ELECTRICAL CHARACTERISTICS

#### **Absolute Maximum Ratings †**

Supply Voltage	+20V
Input Voltage (V <sub>DD</sub> + 0.3V) to	o (GND – 5V)
Input Current (VIN > VDD)	50 mA

† Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operation sections of the specifications is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

#### DC CHARACTERISTICS

Parameters	Sym	Min	Тур	Max	Units	Conditions
Input			71			
Logic '1', High Input Voltage	V <sub>IH</sub>	2.4	1.8	_	V	
Logic '0', Low Input Voltage	V <sub>IL</sub>	_	1.3	0.8	V	
Input Current	I <sub>IN</sub>	-10	_	+10	μA	$0V \le V_{IN} \le V_{DD}$
Input Voltage	V <sub>IN</sub>	<b>-</b> 5		V <sub>DD</sub> – 0.3	V	
Output						
High Output Voltage	V <sub>OH</sub>	V <sub>DD</sub> – 0.025	1	_	V	DC Test
Low Output Voltage	V <sub>OL</sub>		1	0.025	V	DC Test
Output Resistance, High	R <sub>OH</sub>	_	1.25	1.5	Ω	I <sub>OUT</sub> = 10 mA, V <sub>DD</sub> = 18V
Output Resistance, Low	R <sub>OL</sub>	_	8.0	1.1	Ω	I <sub>OUT</sub> = 10 mA, V <sub>DD</sub> = 18V
Peak Output Current	I <sub>PK</sub>	_	10.0	_	Α	V <sub>DD</sub> = 18V
Continuous Output Current	I <sub>DC</sub>	2	_	_	A	$10V \le V_{DD} \le 18V$ , $T_A = +25^{\circ}C$ (TC4421A/TC4422A CAT only) (Note 2)
Latch-Up Protection Withstand Reverse Current	I <sub>REV</sub>	_	>1.5	_	Α	Duty cycle $\leq$ 2%, t $\leq$ 300 µsec
Switching Time (Note 1)						
Rise Time	t <sub>R</sub>	_	28	34	ns	<b>Figure 4-1</b> , C <sub>L</sub> = 10,000 pF
Fall Time	t <sub>F</sub>	_	26	32	ns	<b>Figure 4-1</b> , C <sub>L</sub> = 10,000 pF
Propagation Delay Time	t <sub>D1</sub>	_	38	45	ns	<b>Figure 4-1</b> , C <sub>L</sub> = 10,000 pF
Propagation Delay Time	t <sub>D2</sub>	_	42	49	ns	<b>Figure 4-1</b> , C <sub>L</sub> = 10,000 pF
Power Supply		•				
Power Supply Current	Is	_	130	250	μA	V <sub>IN</sub> = 3V
		_	35	100	μA	$V_{IN} = 0V$
Operating Input Voltage	$V_{DD}$	4.5	_	18	V	

Note 1: Switching times ensured by design.

2: Tested during characterization, not production tested.

#### DC CHARACTERISTICS (OVER OPERATING TEMPERATURE RANGE)

Electrical Specifications: Unless otherwise noted, over operating temperature range with $4.5V \le V_{DD} \le 18V$ .									
Parameters	Sym	Min	Тур	Max	Units	Conditions			
Input									
Logic '1', High Input Voltage	V <sub>IH</sub>	2.4	_	_	V				
Logic '0', Low Input Voltage	$V_{IL}$	_	_	0.8	V				
Input Current	I <sub>IN</sub>	-10	_	+10	μΑ	$0V \le V_{IN} \le V_{DD}$			
Output									
High Output Voltage	V <sub>OH</sub>	V <sub>DD</sub> – 0.025	_	_	V	DC Test			
Low Output Voltage	V <sub>OL</sub>	_	_	0.025	V	DC Test			
Output Resistance, High	R <sub>OH</sub>	_		2.0	Ω	I <sub>OUT</sub> = 10 mA, V <sub>DD</sub> = 18V			
Output Resistance, Low	R <sub>OL</sub>	_		1.6	Ω	I <sub>OUT</sub> = 10 mA, V <sub>DD</sub> = 18V			
Switching Time (Note 1)									
Rise Time	t <sub>R</sub>	_	38	45	ns	<b>Figure 4-1</b> , C <sub>L</sub> = 10,000 pF			
Fall Time	t <sub>F</sub>	_	33	40	ns	<b>Figure 4-1</b> , C <sub>L</sub> = 10,000 pF			
Propagation Delay Time	t <sub>D1</sub>	_	50.4	60	ns	<b>Figure 4-1</b> , C <sub>L</sub> = 10,000 pF			
Propagation Delay Time	t <sub>D2</sub>	_	53	60	ns	<b>Figure 4-1</b> , C <sub>L</sub> = 10,000 pF			
Power Supply									
Power Supply Current	I <sub>S</sub>	_	200	500	μA	V <sub>IN</sub> = 3V			
		_	50	150	μA	V <sub>IN</sub> = 0V			
Operating Input Voltage	$V_{DD}$	4.5		18	V				

Note 1: Switching times ensured by design.

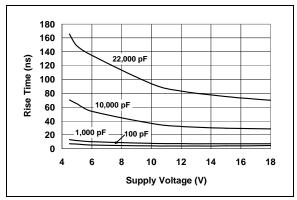
#### **TEMPERATURE CHARACTERISTICS**

<b>Electrical Specifications:</b> Unless otherwise noted, all parameters apply with $4.5V \le V_{DD} \le 18V$ .								
Parameters	Sym	Min	Тур	Max	Units	Conditions		
Temperature Ranges								
Specified Temperature Range (V)	T <sub>A</sub>	-40	_	+125	°C			
Maximum Junction Temperature	TJ	_	_	+150	°C			
Storage Temperature Range	T <sub>A</sub>	-65	_	+150	°C			
Package Thermal Resistances								
Thermal Resistance, 5L-TO-220	$\theta_{JA}$	_	71	_	°C/W	Without heat sink		
Thermal Resistance, 8L-6x5 DFN	$\theta_{JA}$	_	33.2	_	°C/W	Typical 4-layer board with vias to ground plane		
Thermal Resistance, 8L-PDIP	$\theta_{\sf JA}$	_	125	_	°C/W			
Thermal Resistance, 8L-SOIC	$\theta_{\sf JA}$	_	155	_	°C/W			

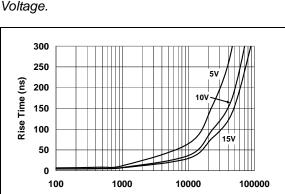
#### 2.0 TYPICAL PERFORMANCE CURVES

**Note:** The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

**Note:** Unless otherwise indicated,  $T_A = +25^{\circ}C$  with 4.5V  $\leq V_{DD} \leq 18V$ .

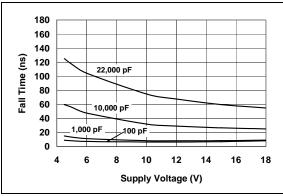


**FIGURE 2-1:** Rise Time vs. Supply Voltage.



**FIGURE 2-2:** Rise Time vs. Capacitive Load.

Capacitive Load (pF)



**FIGURE 2-3:** Fall Time vs. Supply Voltage.

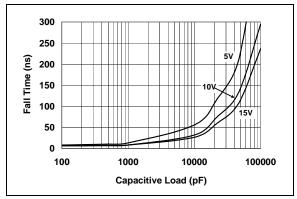


FIGURE 2-4: Fall Time vs. Capacitive Load.

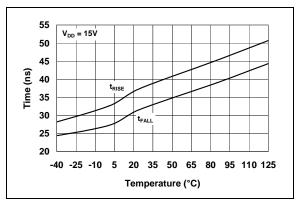


FIGURE 2-5: Rise and Fall Times vs. Temperature.

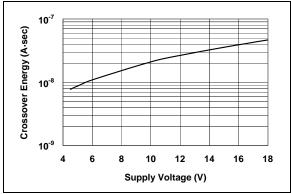
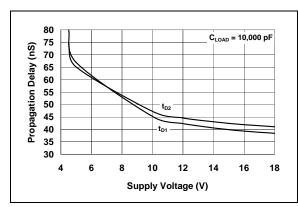
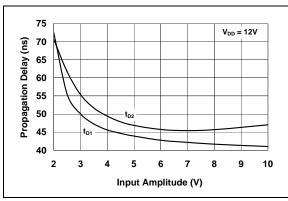


FIGURE 2-6: Crossover Energy vs Supply Voltage.

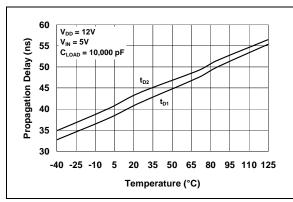
**Note:** Unless otherwise indicated,  $T_A = +25^{\circ}C$  with 4.5V  $\leq V_{DD} \leq 18V$ .



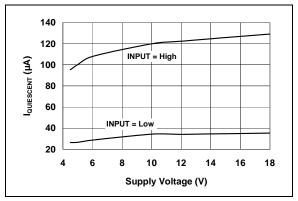
**FIGURE 2-7:** Propagation Delay vs. Supply Voltage.



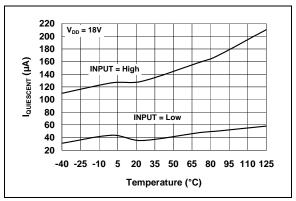
**FIGURE 2-8:** Propagation Delay vs. Input Amplitude.



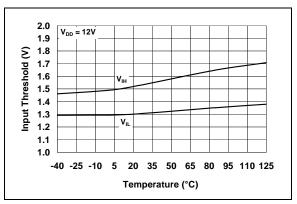
**FIGURE 2-9:** Propagation Delay vs. Temperature.



**FIGURE 2-10:** Quiescent Supply Current vs. Supply Voltage.



**FIGURE 2-11:** Quiescent Supply Current vs. Temperature.



**FIGURE 2-12:** Input Threshold vs. Temperature.

**Note:** Unless otherwise indicated,  $T_A = +25^{\circ}C$  with 4.5V  $\leq V_{DD} \leq 18V$ .

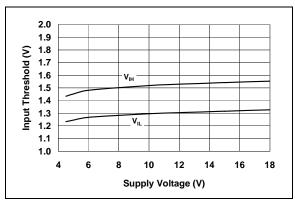
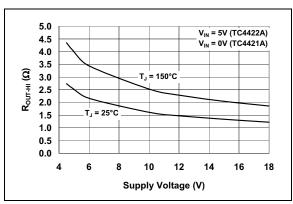


FIGURE 2-13: Input Threshold vs. Supply Voltage.



**FIGURE 2-14:** High-State Output Resistance vs. Supply Voltage.

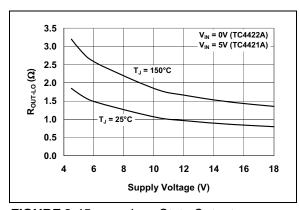
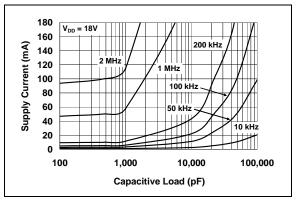
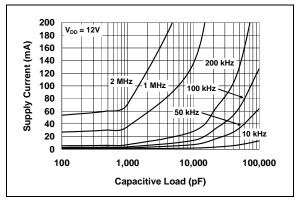


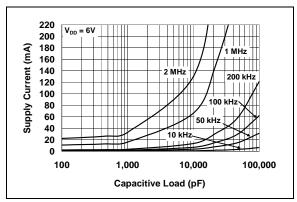
FIGURE 2-15: Low-State Output Resistance vs. Supply Voltage.



**FIGURE 2-16:** Supply Current vs. Capactive Load ( $V_{DD} = 18V$ ).

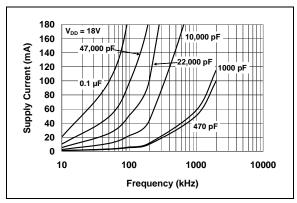


**FIGURE 2-17:** Supply Current vs. Capactive Load ( $V_{DD} = 12V$ ).

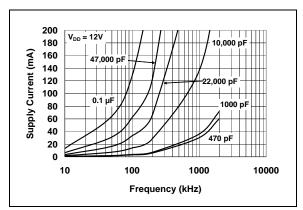


**FIGURE 2-18:** Supply Current vs. Capactive Load  $(V_{DD} = 6V)$ .

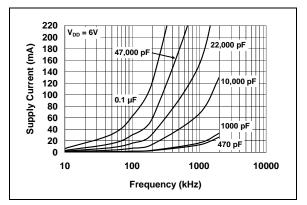
Note: Unless otherwise indicated,  $T_A$  = +25°C with 4.5V  $\leq$  V<sub>DD</sub>  $\leq$  18V.



**FIGURE 2-19:** Supply Current vs. Frequency  $(V_{DD} = 18V)$ .



**FIGURE 2-20:** Supply Current vs. Frequency  $(V_{DD} = 12V)$ .



**FIGURE 2-21:** Supply Current vs. Frequency  $(V_{DD} = 6V)$ .

#### 3.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in Table 3-1.

TABLE 3-1: PIN FUNCTION TABLE

Pin No. 8-Pin PDIP, SOIC	Pin No. 8-Pin DFN	Pin No. 5-Pin TO-220	Symbol	Description
1	1	_	$V_{DD}$	Supply input, 4.5V to 18V
2	2	1	INPUT	Control input, TTL/CMOS-compatible input
3	3	_	NC	No connection
4	4	2	GND	Ground
5	5	4	GND	Ground
6	6	5	OUTPUT	CMOS push-pull output
7	7	_	OUTPUT	CMOS push-pull output
8	8	3	$V_{DD}$	Supply input, 4.5V to 18V
_	PAD	_	NC	Exposed metal pad
_	_	TAB	$V_{DD}$	Metal tab is at the V <sub>DD</sub> potential

#### 3.1 Supply Input (V<sub>DD</sub>)

The  $V_{DD}$  input is the bias supply for the MOSFET driver and is rated for 4.5V to 18V with respect to the ground pin. The  $V_{DD}$  input should be bypassed to ground with a local ceramic capacitor. The value of the capacitor should be chosen based on the capacitive load that is being driven. A minimum value of 1.0  $\mu$ F is suggested.

#### 3.2 Control Input

The MOSFET driver input is a high-impedance, TTL/CMOS-compatible input. The input also has 300 mV of hysteresis between the high and low thresholds that prevents output glitching even when the rise and fall time of the input signal is very slow.

#### 3.3 CMOS Push-Pull Output

The MOSFET driver output is a low-impedance, CMOS, push-pull style output capable of driving a capacitive load with 9.0A peak currents. The MOSFET driver output is capable of withstanding 1.5A peak reverse currents of either polarity.

#### 3.4 Ground

The ground pins are the return path for the bias current and for the high peak currents that discharge the load capacitor. The ground pins should be tied into a ground plane or have very short traces to the bias supply source return.

#### 3.5 Exposed Metal Pad

The exposed metal pad of the 6x5 DFN package is not internally connected to any potential. Therefore, this pad can be connected to a ground plane or other copper plane on a Printed Circuit Board (PCB) to aid in heat removal from the package.

#### 3.6 Metal Tab

The metal tab of the TO-220 package is connected to the  $V_{DD}$  potential of the device. This connection to  $V_{DD}$  can be used as a current carrying path for the device.

#### 4.0 APPLICATIONS INFORMATION

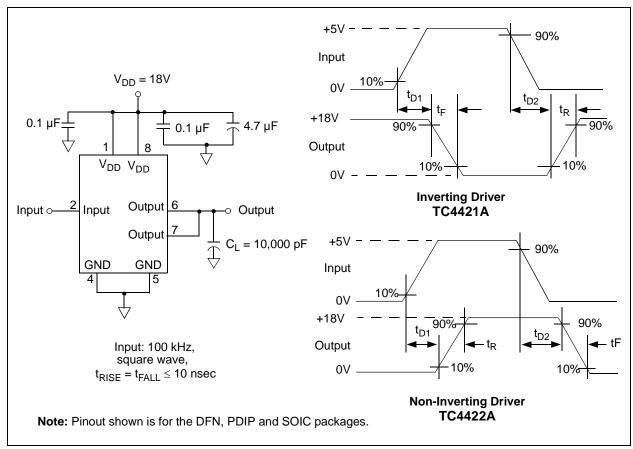


FIGURE 4-1: Switching Time Test Circuits.

#### 5.0 PACKAGING INFORMATION

#### 5.1 Package Marking Information

5-Lead TO-220



8-Lead DFN



8-Lead PDIP (300 mil)



8-Lead SOIC (150 mil)



Example:



Example:



Example:



Example:



Legend: XX...X Customer-specific information

Y Year code (last digit of calendar year)
YY Year code (last 2 digits of calendar year)
WW Week code (week of January 1 is week '01')

NNN Alphanumeric traceability code

e3 Pb-free JEDEC designator for Matte Tin (Sn)

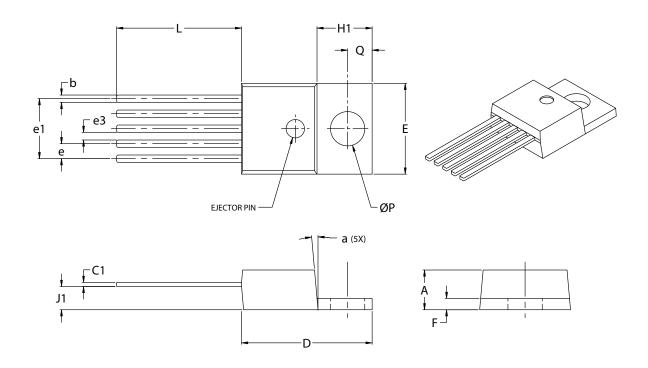
This package is Pb-free. The Pb-free JEDEC designator (e3) can be found on the outer packaging for this package.

**Note**: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available

characters for customer-specific information.

#### 5-Lead Plastic Transistor Outline (AT) (TO-220)

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units			MILLIMETERS		
Dimension Limits		MIN	MAX	MIN	MAX	
Lead Pitch	e	.060	.072	1.52	1.83	
Overall Lead Centers	e1	.263	.273	6.68	6.93	
Space Between Leads	e3	.030	.040	0.76	1.02	
Overall Height	Α	.160	.190	4.06	4.83	
Overall Width	Е	.385	.415	9.78	10.54	
Overall Length	D	.560	.590	14.22	14.99	
Flag Length	H1	.234	.258	5.94	6.55	
Flag Thickness	F	.045	.055	1.14	1.40	
Through Hole Center	Q	.103	.113	2.62	2.87	
Through Hole Diameter	Р	.146	.156	3.71	3.96	
Lead Length	L	.540	.560	13.72	14.22	
Base to Bottom of Lead	J1	.090	.115	2.29	2.92	
Lead Thickness	C1	.014	.022	0.36	0.56	
Lead Width	b	.025	.040	0.64	1.02	
Mold Draft Angle	a	3°	7°	3°	7°	

<sup>\*</sup>Controlling Parameter

Notes:

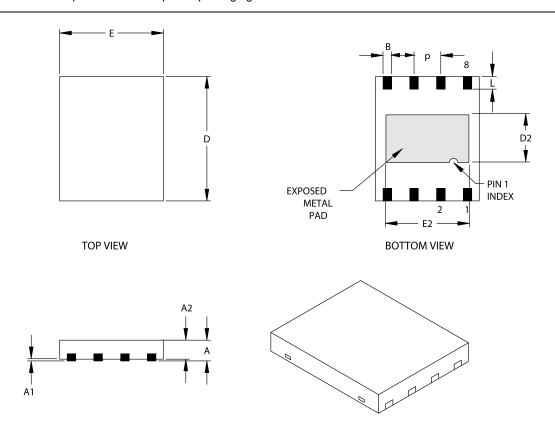
Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" (0.254mm) per side.

JEDEC equivalent: TO-220

Drawing No. C04-036

#### 8-Lead Plastic Dual Flat No Lead Package (MF) 6x5 mm Body (DFN-S) - Saw Singulated

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



		Units		INCHES		M	ILLIMETERS*	
	Dimension Limit	:S	MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins		n		8			8	
Pitch		р		.050 BSC			1.27 BSC	
Overall Height		Α	.033	.035	.037	0.85	0.90	0.95
Package Thickness		A2	.031	.035	.037	0.80	0.89	0.95
Standoff		Α1	.000	.0004	.002	0.00	0.01	0.05
Base Thickness		А3	.007	.008	.009	0.17	0.20	0.23
Overall Length		Е	.195	.197	.199	4.95	5.00	5.05
Exposed Pad Length		E2	.152	.157	.163	3.85	4.00	4.15
Overall Width		D	.234	.236	.238	5.95	6.00	6.05
Exposed Pad Width		D2	.089	.091	.093	2.25	2.30	2.35
Lead Width		В	.014	.016	.019	0.35	0.40	0.47
Lead Length		L	.024		.026	0.60		0.65

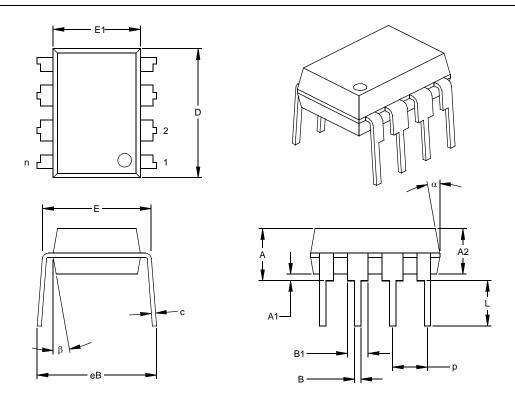
Notes:

JEDEC equivalent: MO-220

Drawing No. C04-122 Revised 11/3/03

#### 8-Lead Plastic Dual In-line (PA) - 300 mil (PDIP)

For the most current package drawings, please see the Microchip Packaging Specification located Note: at http://www.microchip.com/packaging



		Units		INCHES*		N	IILLIMETERS	3
Dimens	sion L	imits	MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins		n		8			8	
Pitch		р		.100			2.54	
Top to Seating Plane		Α	.140	.155	.170	3.56	3.94	4.32
Molded Package Thickness		A2	.115	.130	.145	2.92	3.30	3.68
Base to Seating Plane		A1	.015			0.38		
Shoulder to Shoulder Width		Е	.300	.313	.325	7.62	7.94	8.26
Molded Package Width		E1	.240	.250	.260	6.10	6.35	6.60
Overall Length		О	.360	.373	.385	9.14	9.46	9.78
Tip to Seating Plane		П	.125	.130	.135	3.18	3.30	3.43
Lead Thickness		О	.008	.012	.015	0.20	0.29	0.38
Upper Lead Width		B1	.045	.058	.070	1.14	1.46	1.78
Lower Lead Width		В	.014	.018	.022	0.36	0.46	0.56
Overall Row Spacing	§	eВ	.310	.370	.430	7.87	9.40	10.92
Mold Draft Angle Top		α	5	10	15	5	10	15
Mold Draft Angle Bottom		β	5	10	15	5	10	15

<sup>\*</sup> Controlling Parameter

#### Notes:

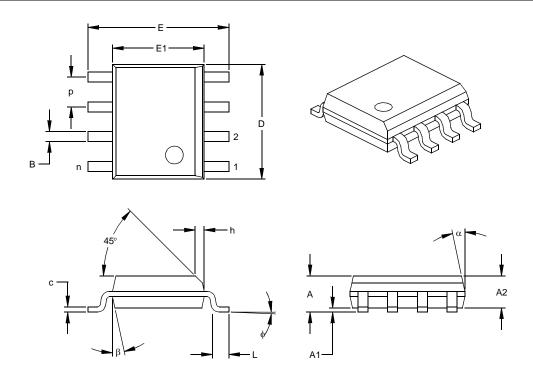
Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" (0.254mm) per side.
JEDEC Equivalent: MS-001

Drawing No. C04-018

<sup>§</sup> Significant Characteristic

#### 8-Lead Plastic Small Outline (OA) - Narrow, 150 mil (SOIC)

For the most current package drawings, please see the Microchip Packaging Specification located Note: at http://www.microchip.com/packaging



	Units		INCHES*		N	IILLIMETERS	3
Dimension	on Limits	MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins	n		8			8	
Pitch	р		.050			1.27	
Overall Height	Α	.053	.061	.069	1.35	1.55	1.75
Molded Package Thickness	A2	.052	.056	.061	1.32	1.42	1.55
Standoff §	A1	.004	.007	.010	0.10	0.18	0.25
Overall Width	Е	.228	.237	.244	5.79	6.02	6.20
Molded Package Width	E1	.146	.154	.157	3.71	3.91	3.99
Overall Length	D	.189	.193	.197	4.80	4.90	5.00
Chamfer Distance	h	.010	.015	.020	0.25	0.38	0.51
Foot Length	L	.019	.025	.030	0.48	0.62	0.76
Foot Angle	ф	0	4	8	0	4	8
Lead Thickness	С	.008	.009	.010	0.20	0.23	0.25
Lead Width	В	.013	.017	.020	0.33	0.42	0.51
Mold Draft Angle Top	α	0	12	15	0	12	15
Mold Draft Angle Bottom	β	0	12	15	0	12	15

Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed

.010" (0.254mm) per side.
JEDEC Equivalent: MS-012

Drawing No. C04-057

<sup>\*</sup> Controlling Parameter § Significant Characteristic

NOTES:

#### **APPENDIX A: REVISION HISTORY**

#### Revision A (May 2005)

• Original Release of this Document.

#### **Revision B (January 2013)**

Added a note to each package outline drawing.

**NOTES:** 

I

#### PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

PART NO. X	<u>xx xxx</u>	Exa	Examples:			
Device Tempe Rar	erature Package Tape & Reel nge	a)	TC4421AVAT: 9A High-Speed Inverting MOSFET Driver, TO-220 package, -40°C to +125°C.			
Device:	TC4421A: 9A High-Speed MOSFET Driver, Inverting TC4422A: 9A High-Speed MOSFET Driver, Non-Inverting	b)	TC4421AVOA: 9A High-Speed Inverting MOSFET Driver, SOIC package, -40°C to +125°C.			
Temperature Range:	V = -40°C to +125°C	c)	TC4421AVMF: 9A High-Speed Inverting MOSFET Driver,			
Package: *	AT = TO-220, 5-lead  MF = Dual, Flat, No-Lead (6x5 mm Body), 8-lead  MF713 = Dual, Flat, No-Lead (6x5 mm Body), 8-lead		DFN package, -40°C to +125°C.			
	(Tape and Reel)  PA = Plastic DIP (300 mil Body), 8-lead  OA = Plastic SOIC (150 mil Body), 8-lead  OA713 = Plastic SOIC (150 mil Body), 8-lead  (Tape and Reel)	a)	TC4422AVPA: 9A High-Speed Non-Inverting MOSFET Driver, PDIP package, -40°C to +125°C.			
	*All package offerings are Pb Free (Lead Free).	b)	TC4422AVOA: 9A High-Speed Non-Inverting MOSFET Driver, SOIC package, -40°C to +125°C.			
		c)	TC4422AVMF: 9A High-Speed Non-Inverting MOSFET Driver, DFN package, -40°C to +125°C.			

NOTES:

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